

Press Release

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IXYS Releases 250V Ultra-Junction X3-Class Power MOSFETs Offering Best-in-Class On-State Resistance and Gate Charge Figure of Merit

Leiden, Netherlands and Milpitas, CA. July 20, 2017 – IXYS Corporation (NASDAQ: IXYS), a global manufacturer of power semiconductors and integrated circuits (ICs) for energy efficiency, power management, transportation, medical, and motor control applications, today announced a new power semiconductor product line: 250V Ultra-Junction X3-Class HiPerFET™ Power MOSFETs. With on-resistances and gate charges as low as 4.5 milliohms and 21 nanocoulombs, respectively, these devices enable highest power densities and energy efficiencies in a wide variety of high-speed power conversion applications.

Developed using a charge compensation principle and proprietary process technology, the new MOSFETs provide the best-in-class Figure of Merit (on-resistance times gate charge) which translates into lowest conduction and switching losses. They exhibit the lowest on-state resistances in the industry (5 milliohms in the TO-264 package and 4.5 milliohms in the SOT-227, for instance).

The fast intrinsic body diodes (HiPerFETs™) of the MOSFETs display very soft recovery characteristics, minimizing voltage overshoots and electromagnetic interference (EMI), especially in half or full-bridge topologies. With low reverse recovery charge and time, the diodes are capable of removing all the leftover energies during high-speed switching to avoid device failure and achieve high efficiency.

Additionally, these new devices are avalanche capable and exhibit a superior dv/dt performance. They are robust against device failure caused by voltage spikes and accidental turn-on of parasitic bipolar transistors inherent in the MOSFET structure. As such, these rugged devices require fewer snubbers and can be used in both hard and soft switching power converters.

Well suited applications include battery chargers for light electric vehicles (LEVs), synchronous rectification in switching power supplies, motor control, DC-DC converters, uninterruptible power supplies, electric forklifts, Class-D audio amplifiers, and telecom systems.

The new 250V X3-Class Power MOSFETs with HiPerFET™ body diodes are available in the following international standard size packages: TO-3P, TO-220 (overmolded or standard), TO-247, PLUS247, TO-252, TO-263, TO-264, TO-268HV, SOT-227. Some example part numbers

include IXFA60N25X3, IXFP80N25X3, IXFT170N25X3HV and IXFK240N25X3, with current ratings of 60A, 80A, 170A, and 240A, respectively.

Additional product information can be obtained by visiting the IXYS website at <http://www.ixys.com> or by contacting the company directly.

About IXYS Corporation

IXYS Corporation makes and markets technology driven products to improve power conversion efficiency, generate solar and wind power, and provide efficient motor controls for industrial applications. IXYS offers a diversified product base that addresses worldwide needs for power control, electrical efficiency, renewable energy, telecommunications, medical devices, electronic displays, and RF power.

Safe Harbor Statement

Any statements contained in this press release that are not statements of historical fact, including the performance, rating, benefits, best-in-class, and suitability of products for various applications, may be deemed to be forward-looking statements. There are a number of important factors that could cause the results of IXYS to differ materially from those indicated by these forward-looking statements, including, among others, risks detailed from time to time in the Company's SEC reports, including its Report on Form 10-K for the fiscal year ended March 31, 2017. The Company undertakes no obligation to publicly release the results of any revisions to these forward-looking statements.